

Silicon NPN Power Transistors

2SC2682

DESCRIPTION

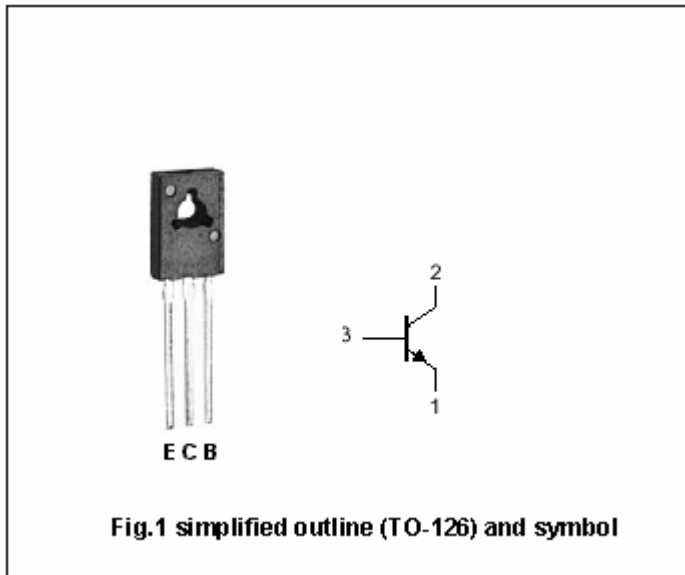
- With TO-126 package
- Complement to type 2SA1142

APPLICATIONS

- Audio frequency power amplifier; high frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	180	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	180	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		0.1	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	1.2	W
		T <sub>C</sub> =25°C	10	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =5mA		0.12	0.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =5mA		0.8	1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =180V; I <sub>E</sub> =0			1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =3V; I <sub>C</sub> =0			1	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1mA; V <sub>CE</sub> =5V	90	190		
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =10mA; V <sub>CE</sub> =5V	100	200	320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =20mA; V <sub>CE</sub> =10V		200		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		3.2		pF

◆ h<sub>FE-2</sub> Classifications

Q	P
100-200	160-320

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PACKAGE OUTLINE

